2018년 2월 7일(수), 10:45-12:15 Room I (청옥II+III, 6층)

## K. Memory (Design & Process Technology) 분과 [WI2-K] ReRAM II - New Technologies

WI2-K-1 10:45-11:15	[초청] Halide perovskites for Low Voltage Resistive Switching Memories Ho Won Jang Department of Materials Science and Engineering, Seoul National University
WI2-K-2 11:15-11:30	Thermally Stable Resistive Switching Characteristics of Te-Based Conductive-Bridge Memoryby Optimizing Zr-Te Composition Sangmin Lee, Seokjae Lim, Jeonghwan Song, Jaehyuk Park, and Hyunsang Hwang Department of MS&E, POSTECH
WI2-K-3 11:30-11:45	Fabrication of Cu Cone Structure Embedded CBRAM Array for Inducing Field Concentration Effect & Material Limited Switching Effect Hae Jin Kim <sup>1</sup> , Tae Hyung Park <sup>1</sup> , Young Jae Kwon <sup>1</sup> , Dae Eun Kwon <sup>1</sup> , Yu Min Kim <sup>1</sup> , Tae Jung Ha <sup>2</sup> , Soo Gil Kim <sup>2</sup> , and Cheol Seong Hwang <sup>1</sup> **Department of Materials Science and Engineering and Inter-University Semiconductor Research Center, Seoul National University, <sup>2</sup> SK Hynix Inc.
WI2-K-4 11:45-12:00	The Effect of Au Nanodots Geometry and Location in the Pt/Ta <sub>2</sub> O <sub>5</sub> /HfO2-x/TiN Structure  Young Jae Kwon, Jung Ho Yoon, Yu Min Kim, Dae Eun Kwon, Tae Hyung Park, Hae Jin Kim, Kyung Seok Woo, Tae Gyun Park, and Cheol Seong Hwang  Department of Materials Science and Engineering and Inter-university  Semiconductor Research Center, Seoul National University
WI2-K-5 12:00-12:15	Self-Rectifying Resistive Random-Access Memory with a-Si/Si <sub>3</sub> N <sub>4</sub> Bilayer Hui Tae Kwon, Won Joo Lee, Hyun-seok Choi, Daehoon Wee, Yu Jeong Park, Boram Kim, and Yoon Kim Department of Nano-Energy Engineering, BK21 Plus Nano-convergence Technology Division, Pusan National University